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		DB	003/03/26
		720	103/03/
		USPAT;	3:36
	wits Search Text	EPO; JPO; 1.	122/26
	Hits Search	TBM TUP 12	003/03/26
	"self-allyno"	1 1 1	3:41
Number	Hits Search Text  11082 SAC or "self-aligned contact"  (SAC or "self-aligned contact") and bias  44 (SAC or "self-aligned contact") and sidewall	1 - 700, 1	1
	11000   and contact"	IBM_TDB	2003/03/26
	"salf-aligned of	1	14:34
1 1	(SAC or "sell and sidewall and endpoint and or opening or via) and sidewall (contact or opening or electrode) and spacer and (gate or electrode)	1 - 100, 1	
1	(SAC of and endpoint and sidewall and endpoint and or via) and sidewall	EPO	2003/03/26
2	anening or Via,	IBM_TDB	2003/03/
1-	I mantact or opening or elect	USPAT;	14:08
1	and endpoint and endpoint  (contact or opening or via) and sideward  (contact or opening or via) and sideward  (contact or opening or via) and sideward  (and spacer and (gate or electrode) and  endpoint (bias adj voltage) same endpoint (bias adj voltage) same endpoint	EPO; JPO;	
\ 3	and sport	TRM TUD	2003/03/26
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	and endpoint	IBM_TDB	2003/03/26
\ 4	151 (bias adj voltage) and endpoint	1 nam:	1 1
1	(bias ad) voltage (bias ad) voltage or via) and spacer and contact or opening or via) and endpoint (contact or electrode) and endpoint and spacer	EPO; JPO;	
1	151   (blue and space)	EPO, TDB	2003/03/26
\ 5	mening or Viar endpoint	IBM TDB	2003/03/
1	(contact or opening or via) and spacer and (gate or electrode) and endpoint and spacer and (gate or electrode) and spacer	USPAT;	15:42
1	401 (contact of opening or via) and spacer and (contact or opening or via) and bias and gate or electrode) and bias and	EPO; JPO;	102/26
\6	and (gate of or opening or via) and spaces  (contact or opening or via) and bias and  and (gate or electrode) and bias and and (gate or electrode)	IBM_TDB	1 2003/03/20
10	tagt or opening and bit	USPAT	16:24
1	76 (contact or electron	1	12003/03/20
\	and (gate	USPAT;	1 4 7 . () 1
\7	endpoint colectric	or USPATION	J, \
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1	("silicon oxide" or SiO or draw and "silicon oxide" or SiO or draw and "silicon and polysilicon and ("silicon oxide" or TEOS) and insulating) and polysilicate or TEOS) and (tera and spacer and (bias adj voltage) and endpoint) and spacer and spacer and endpoint) and the and spacer and s	1 1 1 1 1 1 1 1	2003/03/26
\ 8	"silicon oxid polysilicor TEOS) and	e) USPAT;	
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1	("silicon oxide polysilicon TEOS) and insulating) and polysilicate or TEOS) and (tetraethylorthosilicate or determined (tetraethylorthosilicate and spacer and (bias adj voltage) and endpoint) and (bias adj voltage) and endpoint) and (bias adj voltage)		
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